

### General Description

The WST3034 is the highest performance trench N-ch MOSFET with extreme high cell density, which provide excellent R<sub>DS(on)</sub> and gate charge for most of the small power switching and load switch applications.

The WST3034 meet the RoHS and Green Product requirement with full function reliability approved.

### Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent C<sub>dv/dt</sub> effect decline
- Green Device Available

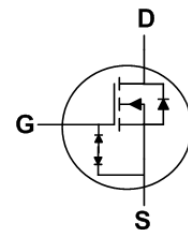
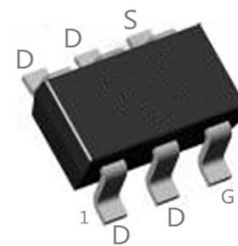
### Product Summary

BVDSS	R <sub>DS(on)</sub>	I <sub>D</sub>
20V	22mΩ	6.9A

### Applications

- Power Management in Notebook Computer, Portable Equipment and Battery Powered Systems.
- ESD:2KV

### SOT-23-6L Pin Configuration



### Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	20	V
V <sub>GS</sub>	Gate-Source Voltage	±12	V
I <sub>D@T<sub>A</sub>=25°C</sub>	Continuous Drain Current, V <sub>GS</sub> @ 4.5V <sup>1</sup>	6.9	A
I <sub>D@T<sub>A</sub>=70°C</sub>	Continuous Drain Current, V <sub>GS</sub> @ 4.5V <sup>1</sup>	4.9	A
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	20	A
P <sub>D@T<sub>A</sub>=25°C</sub>	Total Power Dissipation <sup>3</sup>	2.1	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C

### Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R <sub>θJA</sub>	Thermal Resistance Junction-ambient <sup>1</sup>	---	150	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-Case <sup>1</sup>	---	70	°C/W

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	20	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BVDSS Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	---	0.022	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =6.2A	---	20	24	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =5.2A	---	26	32	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	0.5	0.7	1.5	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-2.33	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =16V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =16V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±12V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =5A	---	18	---	S
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz	---	1.5	3	Ω
Q <sub>g</sub>	Total Gate Charge (4.5V)	V <sub>DS</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =6.2A	---	12	17	nC
Q <sub>gs</sub>	Gate-Source Charge		---	1.4	2.0	
Q <sub>gd</sub>	Gate-Drain Charge		---	2.3	3.2	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =10V, V <sub>GEN</sub> =4.5V, R <sub>G</sub> =6Ω I <sub>D</sub> =5A, R <sub>L</sub> =10Ω	---	5	10	ns
T <sub>r</sub>	Rise Time		---	9	17	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	25	46	
T <sub>f</sub>	Fall Time		---	5	10	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1MHz	---	600	800	pF
C <sub>oss</sub>	Output Capacitance		---	135	180	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	125	175	

**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,4</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	1.4	A
I <sub>SM</sub>	Pulsed Source Current <sup>2,4</sup>		---	---	20	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1.3	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =6.2A, dI/dt=100A/μs, T <sub>J</sub> =25°C	---	16	---	nS
Q <sub>rr</sub>	Reverse Recovery Charge		---	10	---	nC

Note :

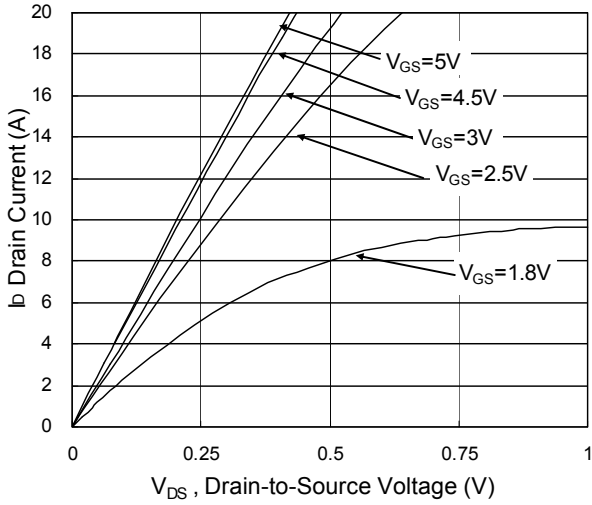
1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.

2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%

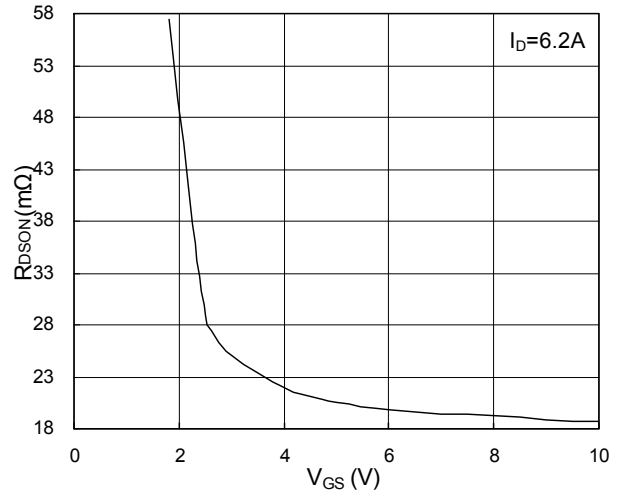
3.The power dissipation is limited by 150°C junction temperature

4.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub>, in real applications, should be limited by total power dissipation.

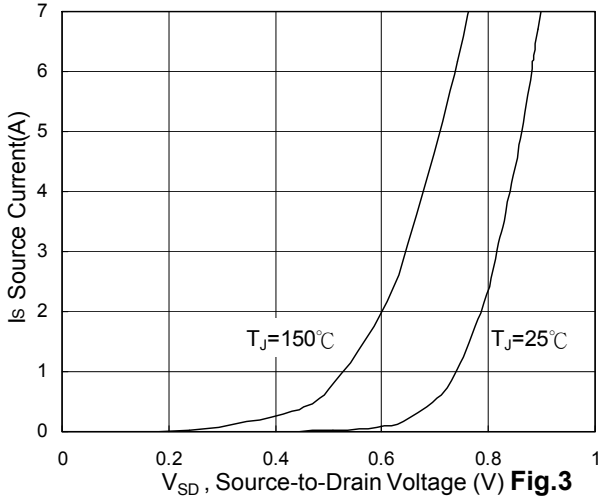
**Typical Characteristics**



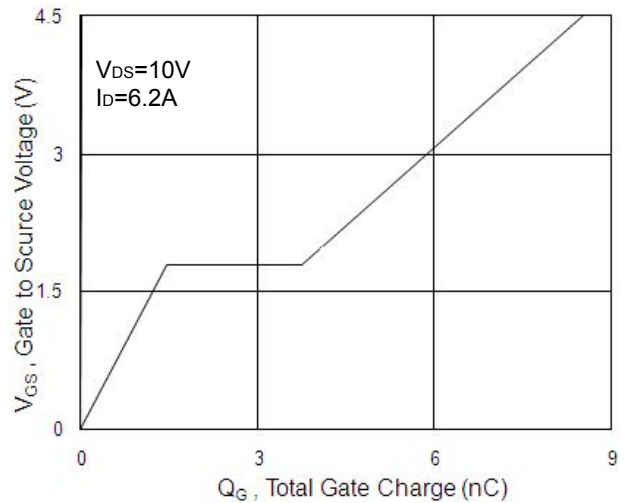
**Fig.1 Typical Output Characteristics**



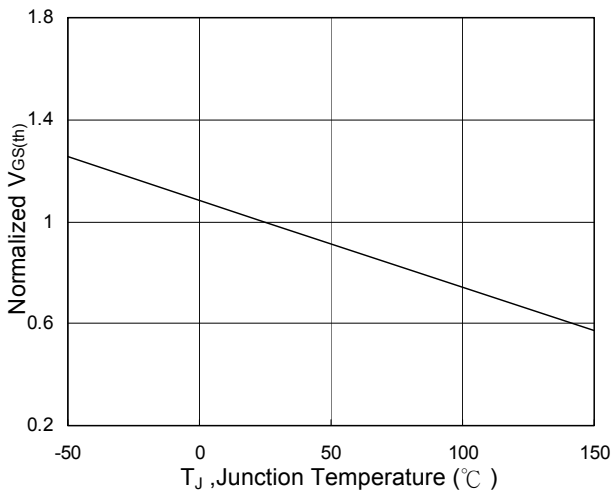
**Fig.2 On-Resistance vs. Gate-Source**



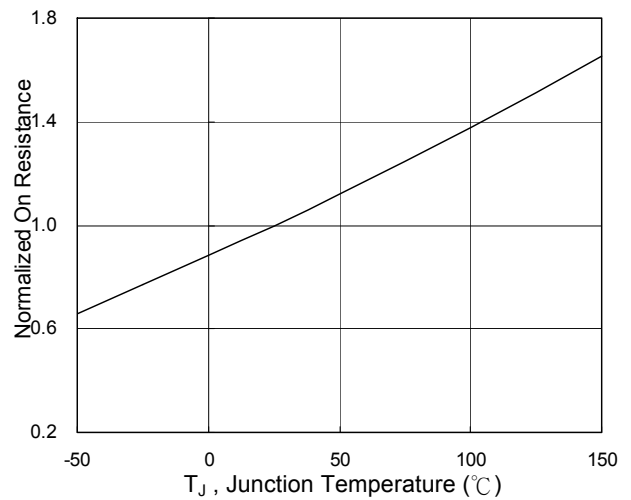
**Forward Characteristics Of Reverse**



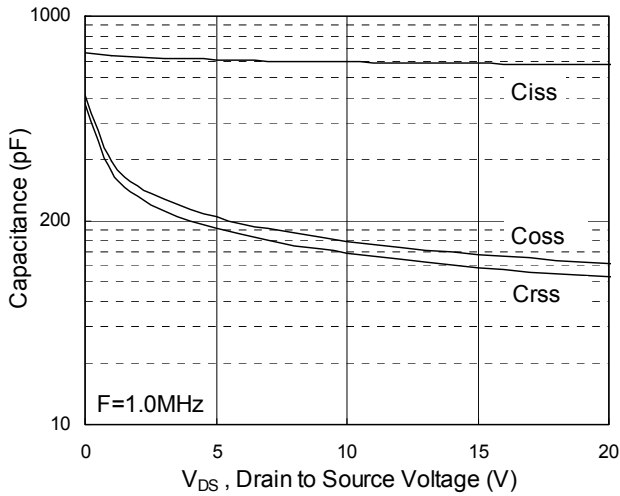
**Fig.4 Gate-Charge Characteristics**



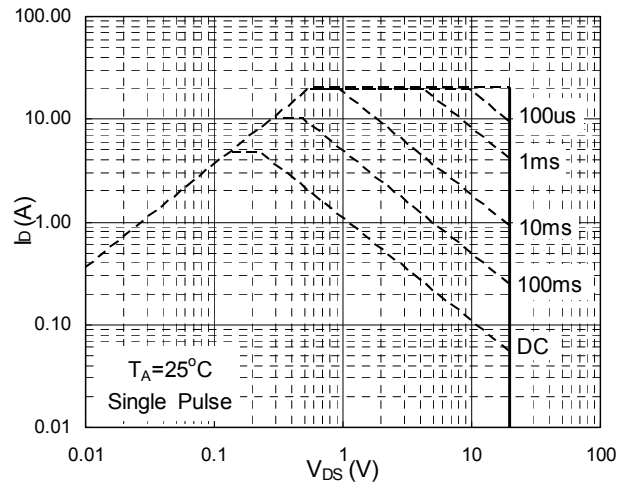
**Fig.5 Normalized V<sub>GS(th)</sub> vs. T<sub>J</sub>**



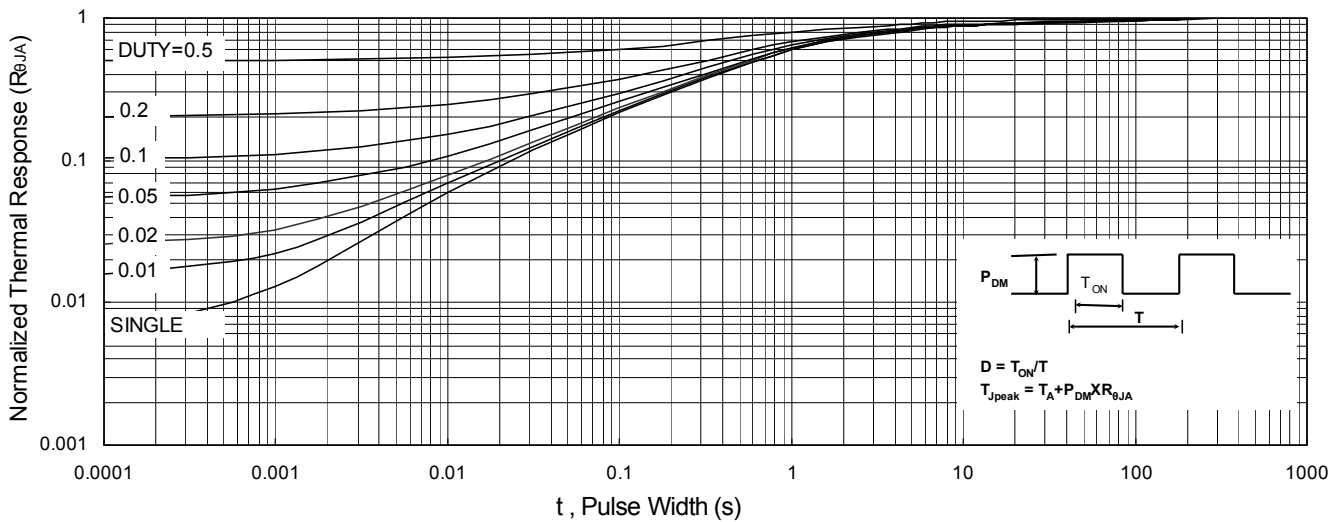
**Fig.6 Normalized R<sub>DS(on)</sub> vs. T<sub>J</sub>**



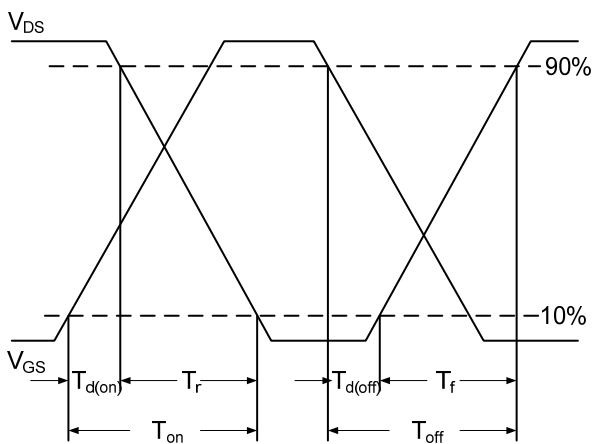
**Fig.7 Capacitance**



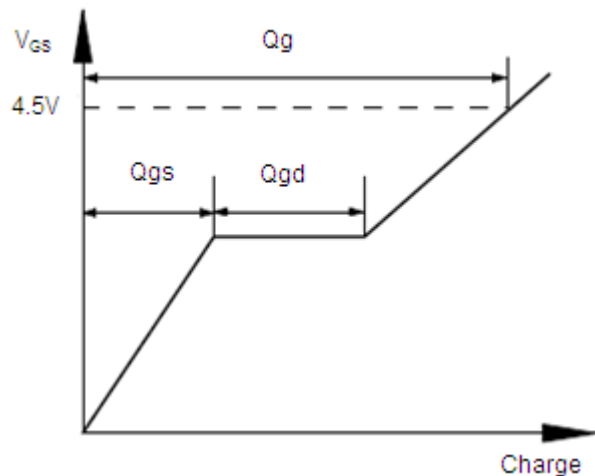
**Fig.8 Safe Operating Area**



**Fig.9 Normalized Maximum Transient Thermal Impedance**



**Fig.10 Switching Time Waveform**



**Fig.11 Gate Charge Waveform**